

Title (en)  
SEMICONDUCTOR STRUCTURES HAVING A COMPLIANT SUBSTRATE

Title (de)  
HALBLEITERSTRUKTUREN MIT EINEM NACHGIEBIGEN SUBSTRAT

Title (fr)  
STRUCTURES SEMI-CONDUCTRICES A SUBSTRAT FLEXIBLE

Publication  
**EP 1348231 A2 20031001 (EN)**

Application  
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Priority  
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• US 72156600 A 20001122

Abstract (en)  
[origin: WO0245140A2] High quality epitaxial layers of monocrystalline materials can be grown overlying monocrystalline substrates such as large silicon wafers by forming a compliant substrate for growing the monocrystalline layers. One way to achieve the formation of a compliant substrate includes first growing an accommodating buffer layer (24) on a silicon wafer (22). The accommodating buffer layer is a layer of monocrystalline oxide spaced apart from the silicon wafer by an amorphous interface layer (28) of silicon oxide. The amorphous interface layer dissipates strain and permits the growth of a high quality monocrystalline oxide accommodating buffer layer. The accommodating buffer layer is lattice matched to both the underlying silicon wafer and the overlying monocrystalline material layer (26). Any lattice mismatch between the accommodating buffer layer and the underlying silicon substrate is taken care of by the amorphous interface layer. In addition, formation of a compliant substrate may include utilizing surfactant enhanced epitaxy, epitaxial growth of single crystal silicon onto single crystal oxide, and epitaxial growth of Zintl phase materials.

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